

TL103Wx Dual Operational Amplifiers With Internal Reference

1 Features

- New **TL103WB**, a pin-compatible upgrade to the TL103W and TL103WA
- Improved specifications of B version amplifiers:
 - Supply range: 3 V to 36 V
 - Low maximum input offset voltage: ± 3 mV (25°C) and ± 4 mV (full temperature)
 - Gain bandwidth: 1.2 MHz
 - Total supply current: 600 μ A
 - EMI rejection: integrated RF and EMI filter
 - Temperature range: -40°C to 125°C
- Improved specifications of B version reference:
 - Fixed 2.5-V reference
 - Tight tolerance maximum of 0.4% (25°C) and 0.8% (full temperature)
 - Wide sink-current range: 0.5 mA (typical) to 100 mA

2 Applications

- **Battery chargers**
- Switch-mode power supplies
- Linear voltage regulation
- **Data-acquisition systems**

3 Description

The TL103Wx devices combine the building blocks of a dual operational amplifier and a fixed voltage reference – both of which are often used in the control circuitry of both switch-mode and linear power supplies. OP AMP1 has its non-inverting input internally tied to a fixed 2.5-V reference, while OP AMP2 is independent, with both inputs uncommitted.

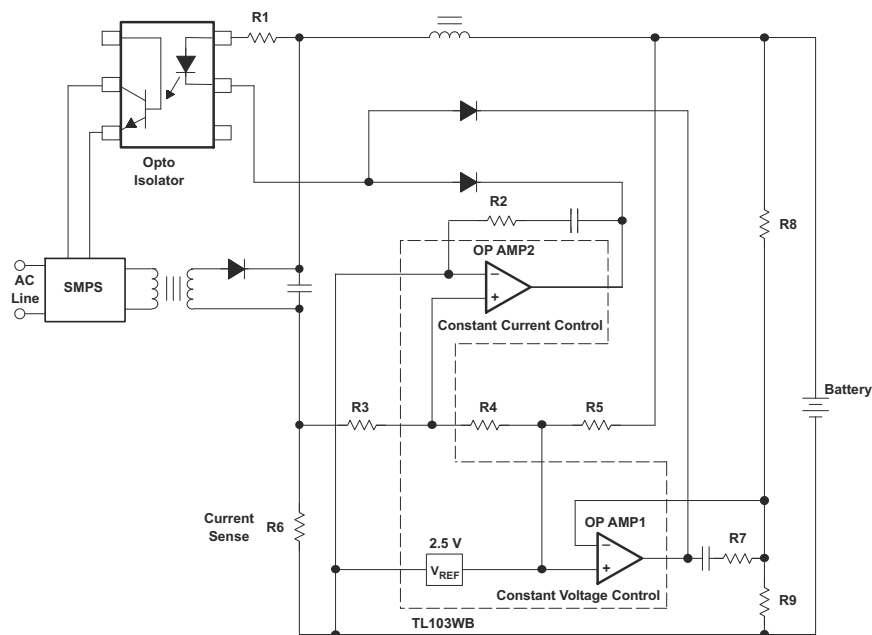
The upgraded TL103WB features improvements such as a wider supply range (up to 36 V), lower supply current (300 μ A) and tighter voltage regulation. This regulation can be achieved through low offset voltages for both operational amplifiers (0.3 mV typical) and tight tolerances for the voltage reference (0.4% at 25°C and 0.8% over operating temperature range).

The TL103WB has a widened temperature range of -40°C to 125°C.

Device Information

PART NUMBER	CHANNEL COUNT	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽³⁾
TL103W	Dual + Reference	D (SOIC, 8) ⁽²⁾	4.9 mm × 6 mm
TL103WA		DDF (SOT-23, 8) ⁽²⁾	2.9 mm × 2.8 mm
TL103WB			

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) This package is preview only.
- (3) The package size (length × width) is a nominal value and includes pins, where applicable.



Typical Application Circuit



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4 Revision History

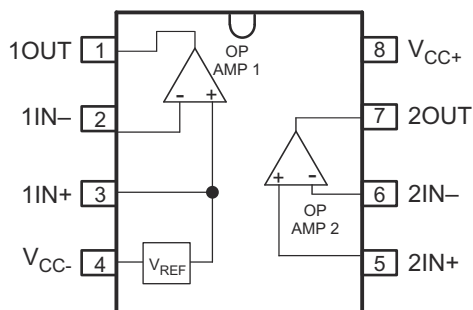
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision M (October 2016) to Revision N (August 2023)	Page
• Updated <i>Features</i> section to highlight TL103WB.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Added the <i>TL103WB</i> device information throughout the document.....	1
• Updated <i>Description</i> section.....	1
• Updated <i>Device Information</i> table to include channel count.....	1
• Removed DRJ package details and added DDF package for preview.....	3
• Updated formatting for <i>Electrical Characteristics</i> tables.....	5
• Updated typical dynamic impedance from 0.2 Ω to 0.4 Ω in <i>Electrical Characteristics</i> tables	5

Changes from Revision L (February 2016) to Revision M (October 2016)	Page
• Changed positive and negative terminals OP AMP 2 in the D Package image of <i>Pin Configuration and Functions</i>	3

Changes from Revision K (October 2010) to Revision L (February 2016)	Page
• Added the <i>Device Information</i> table, <i>Pin Configuration and Functions</i> , <i>ESD Ratings</i> , <i>Thermal Information</i> , <i>Device and Documentation Support</i> , and <i>Mechanical, Packaging, and Orderable Information</i> sections.....	1
• Changed <i>Features</i> from: 2 kV ESD Protection (HBM) to: 2.5-kV ESD Protection (HBM).....	1
• Changed the Zener diode component to V_{REF} in the <i>Typical Application Circuit</i>	1
• Changed the Zener diode component to V_{REF} in the D Package of <i>Pin Configuration and Functions</i>	3

5 Pin Configuration and Functions



**Figure 5-1. D and DDF Packages,
8-Pin SOIC and SOT-23-THN
(Top View)**

Table 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1OUT	1	O	Opamp 1 output
1IN-	2	I	Opamp 1 inverting input
1IN+	3	I	Opamp 1 non-inverting input and Shunt reference cathode terminal
V _{CC-}	4	I	Negative Supply Voltage
2IN+	5	I	Opamp 2 non-inverting input
2IN-	6	I	Opamp 2 inverting input
2OUT	7	O	Opamp 2 output
V _{CC+}	8	I	Positive Supply Voltage

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
$V_{CC\pm}$	Supply voltage	TL103W/TL103WA	0	36	V
		TL103WB	0	40	
V_{ID}	Operational amplifier input differential voltage			36	V
V_I	Operational amplifier input voltage range	TL103W/TL103WA	-0.3	36	V
		TL103WB	-0.3	40	
I_{KA}	Voltage reference cathode current			100	mA
T_J	Maximum junction temperature			150	°C
T_{stg}	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
$V_{CC\pm}$	Supply voltage	TL103W/TL103WA	3	32	V
		TL103WB	3	36	
V_{ICR}	Input common-mode voltage range		V_{CC-}	$(V_{CC+}) - 2$	V
I_K	Cathode current		1	100	mA
T_A	Operating free-air temperature	TL103W/TL103WA	-40	105	°C
		TL103WB	-40	125	

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TL103Wx	UNIT
		D (SOIC)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics: OP AMP1 (V_{REF} at Non-Inverting Input)

V_{CC+} = 5 V, V_{CC-} = GND, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A	MIN	TYP	MAX	UNIT
AMPLIFIER								
V _{IO}	Input offset voltage	V _{ICM} = 0 V	TL103W		±1	±4	mV	
				Full range	±5			
				TL103WA	±0.5	±3.0		
				Full range	±5			
			TL103WB	±0.3	±3.0			
			Full range	±4				
αV _{IO}	Input offset-voltage drift		TL103W/TL103WA	Full range	±7		μV/°C	
			TL103WB	Full range	±3.5			
I _{IB}	Input bias current (negative input)		TL103W/TL103WA		±20		nA	
			TL103WB		±10			
A _{VD}	Large-signal voltage gain	V _{CC+} = 15 V, R _L = 2 kΩ, V _{ICM} = 0 V	TL103W/TL103WA		100		V/mV	
			TL103WB		140			
k _{SVR}	Supply-voltage rejection ratio	V _{CC+} = 5 V to 30 V, V _{ICM} = 0 V	TL103W/TL103WA		65	100	dB	
			TL103WB		80	114		
I _O	Output current	V _{CC+} = 15 V, V _O = 2 V, V _{ID} = 1 V	Source ⁽¹⁾		20	40	mA	
			Sink ⁽¹⁾		10	12		
		V _{CC+} = 15 V, V _O = 0.2 V, V _{ID} = -1 V	Sink ⁽¹⁾	TL103W/TL103WA		12	50	μA
				TL103WB		60	100	
I _{SC}	Short-circuit to GND	V _{CC+} = 15 V			±40	±60	mA	
V _O	Voltage output swing from rail	V _{CC+} = 30 V, R _L = 2 kΩ	Positive Rail (V _{CC+})	TL103W/TL103WA		26	27	V
				Full range		26		
			TL103WB		27.4	28.4		
				Full range		27.4		
		V _{CC+} = 30 V, R _L = 10 kΩ	Positive Rail (V _{CC+})	TL103W/TL103WA		27	28	
				Full range		27		
			TL103WB		27.6	28.6		
				Full range		27.6		
			Negative Rail (V _{CC-})			5	20	mV
				Full range			20	
SR	Slew rate at unity gain	V _{CC+} = 15 V, C _L = 100 pF, R _L = 2 kΩ, V _I = 0.5 V to 2 V, unity gain	TL103W/TL103WA		0.2	0.4	V/μs	
			TL103WB		0.2	0.5		
GBW	Gain bandwidth product	V _{CC+} = 30 V, V _I = 10 mV, C _L = 100 pF, R _L = 2 kΩ, f = 100 kHz	TL103W/TL103WA		0.5	0.9	MHz	
			TL103WB		0.5	1.2		
THD	Total harmonic distortion	V _{CC+} = 30 V, V _O = 2 V _{PP} , C _L = 100 pF, R _L = 2 kΩ, f = 1 kHz, A _V = 20 dB	TL103W/TL103WA		0.02		%	
			TL103WB		TBD			
I _{CC}	Total supply current, excluding cathode-current reference (both amplifiers)	V _{CC+} = 5 V, no load	TL103W/TL103WA		0.7	1.2	mA	
		V _{CC+} = 30 V, no load		Full range		2		
		V _{CC+} = 5 V, no load	TL103WB		0.6	0.92		
		V _{CC+} = 30 V, no load		Full range		1.6		
VOLTAGE REFERENCE								
V _{ref}	Reference Voltage	I _K = 10 mA	TL103W		2.482	2.5	2.518	V
				Full Range	2.465		2.535	V
			TL103WA/TL103WB		2.49	2.5	2.51	V
				Full Range	2.48		2.52	V
ΔV _{ref}	Reference input voltage deviation over temperature range	I _K = 10 mA		Full Range		7	30	mV
I _{min}	Minimum cathode current for regulation					0.5	1	mA
Z _{KA}	Dynamic impedance	I _{KA} = 1 mA to 100 mA, f < 1 kHz				0.4	0.5	Ω

(1) Specified by characterization only

6.6 Electrical Characteristics: OP AMP2 (Independent Amplifier)

$V_{CC+} = 5\text{ V}$, $V_{CC-} = \text{GND}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A	MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_{ICM} = 0\text{ V}$	TL103W		± 1	± 4		mV
				Full range			± 5	
			TL103WA		± 0.5	± 3.0		
				Full range			± 5	
αV_{IO}	Input offset-voltage drift		TL103W/TL103WA	Full range	± 7			$\mu\text{V}/^\circ\text{C}$
			TL103WB	Full range	± 3.5			
I_{IO}	Input offset current		TL103W/TL103WA		± 2	± 75		nA
				Full range			± 150	
			TL103WB		± 0.5	± 4		
				Full range			± 5	
I_{IB}	Input bias current		TL103W/TL103WA		± 20	± 150		nA
				Full range			± 200	
			TL103WB		± 10	± 10		
				Full range			± 50	
A_{VD}	Large-signal voltage gain	$V_{CC+} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_O = 1.4\text{ V}$ to 11.4 V	TL103W/TL103WA		50	100		V/mV
					25	100		
			TL103WB		70	140		
					35	140		
k_{SVR}	Supply-voltage rejection ratio	$V_{CC+} = 5\text{ V}$ to 30 V	TL103W/TL103WA		65	100		dB
			TL103WB		80	114		
V_{ICR}	Input common-mode voltage range	$V_{CC+} = 30\text{ V}$			V_{CC-}	$(V_{CC+}) - 1.5$		V
				Full range	V_{CC-}	$(V_{CC+}) - 2$		
CMRR	Common-mode rejection ratio	$V_{CC+} = 30\text{ V}$	TL103W/TL103WA		70	85		dB
				Full range	60			
I_O	Output current	$V_{CC+} = 15\text{ V}$, $V_O = 2\text{ V}$	Source, $V_{ID} = 1\text{ V}^{(1)}$		20	40		mA
			Sink, $V_{ID} = -1\text{ V}^{(1)}$		10	12		
		$V_{CC+} = 15\text{ V}$, $V_O = 0.2\text{ V}$, $V_{ID} = -1\text{ V}$	Sink ⁽¹⁾	TL103W/TL103WA	12	50		μA
				TL103WB	60	100		
I_{SC}	Short-circuit to GND	$V_{CC+} = 15\text{ V}$			± 40	± 60		mA
V_O	Voltage output swing from rail	$V_{CC+} = 30\text{ V}$, $R_L = 2\text{ k}\Omega$	Positive Rail (V_{CC+})	TL103W/TL103WA	26	27		V
				Full range	26			
			TL103WB		27.4	28.4		
				Full range	27.4			
		$V_{CC+} = 30\text{ V}$, $R_L = 10\text{ k}\Omega$	Positive Rail (V_{CC+})	TL103W/TL103WA	27	28		
				Full range	27			
			TL103WB		27.6	28.6		
				Full range	27.6			
			Negative Rail (V_{CC-})			5	20	mV
				Full range			20	
SR	Slew rate at unity gain	$V_{CC+} = 15\text{ V}$, $C_L = 100\text{ pF}$, $R_L = 2\text{ k}\Omega$, $V_I = 0.5\text{ V}$ to 2 V , unity gain	TL103W/TL103WA		0.2	0.4		V/ μs
			TL103WB		0.2	0.5		
GBW	Gain bandwidth product	$V_{CC+} = 30\text{ V}$, $V_I = 10\text{ mV}$, $C_L = 100\text{ pF}$, $R_L = 2\text{ k}\Omega$, $f = 100\text{ kHz}$	TL103W/TL103WA		0.5	0.9		MHz
			TL103WB		0.5	1.2		
THD	Total harmonic distortion	$V_{CC+} = 30\text{ V}$, $V_O = 2\text{ V}_{PP}$, $C_L = 100\text{ pF}$, $R_L = 2\text{ k}\Omega$, $f = 1\text{ kHz}$, $A_V = 20\text{ dB}$	TL103W/TL103WA		0.02			%
			TL103WB		TBD			
V_n	Equivalent input noise voltage	$V_{CC+} = 30\text{ V}$, $R_S = 100\text{ }\Omega$, $f = 1\text{ kHz}$	TL103W/TL103WA		50			nV/ $\sqrt{\text{Hz}}$
			TL103WB		38			

6.6 Electrical Characteristics: OP AMP2 (Independent Amplifier) (continued)

$V_{CC+} = 5\text{ V}$, $V_{CC-} = \text{GND}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A	MIN	TYP	MAX	UNIT
I_{CC}	Total supply current, excluding cathode-current reference (both amplifiers)	$V_{CC+} = 5\text{ V}$, no load	TL103W/TL103WA			0.7	1.2	mA
		$V_{CC+} = 30\text{ V}$, no load		Full range			2	
		$V_{CC+} = 5\text{ V}$, no load	TL103WB			0.6	0.92	
		$V_{CC+} = 30\text{ V}$, no load		Full range			1.6	

(1) Specified by characterization only

6.7 Typical Characteristics: TL103WB

at $T_A \approx 25^\circ\text{C}$, $V_{CC} = 36\text{ V}$ ($\pm 18\text{ V}$), $V_{CM} = V_{CC} / 2$, $R_{LOAD} = 10\text{ k}\Omega$ connected to $V_{CC} / 2$ (unless otherwise noted)

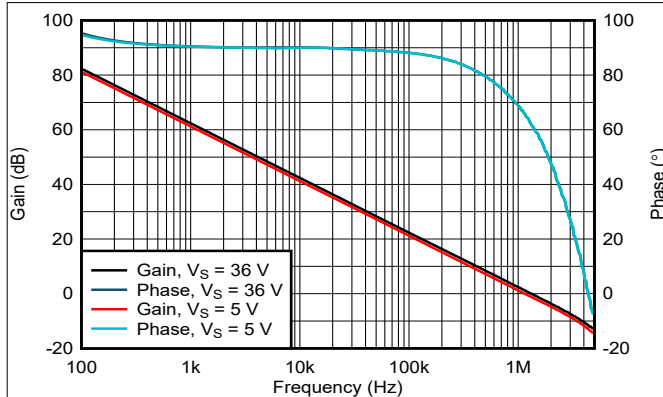


Figure 6-1. Open-Loop Gain and Phase vs Frequency

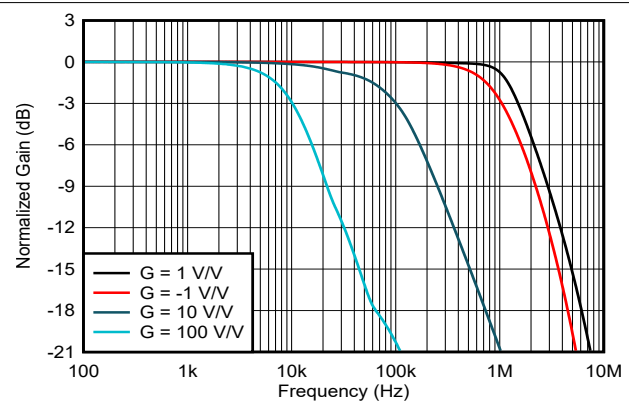


Figure 6-2. Closed-Loop Gain vs Frequency

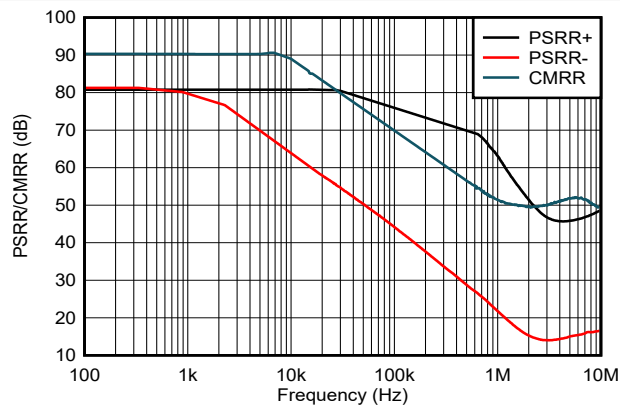


Figure 6-3. CMRR and PSRR vs Frequency

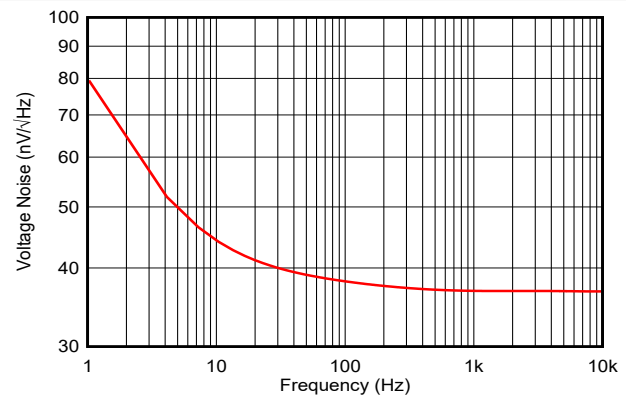


Figure 6-4. Input Voltage Noise Spectral Density vs Frequency

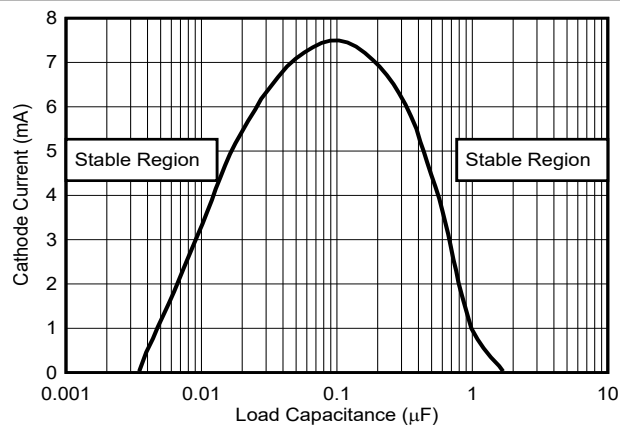


Figure 6-5. Reference Stability vs Capacitive Load

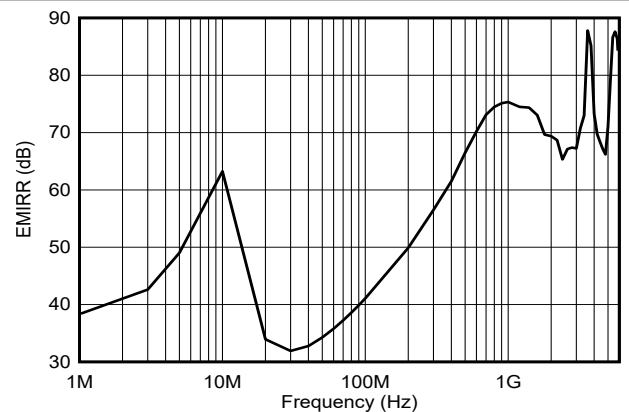


Figure 6-6. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

7 Device and Documentation Support

7.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

7.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

8 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TL103WAID	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103WA	
TL103WAIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103WA	Samples
TL103WID	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	
TL103WIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL103WAIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TL103WIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL103WAIDR	SOIC	D	8	2500	340.5	336.1	25.0
TL103WIDR	SOIC	D	8	2500	340.5	336.1	25.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
TL103WAID	D	SOIC	8	75	507	8	3940	4.32
TL103WID	D	SOIC	8	75	507	8	3940	4.32

D0008A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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